

IN THE SPECIFICATION:

Page 9, line 2, after "ammonia" delete "water".

IN THE CLAIMS:

Please cancel claims 5 and 16.

Please amend claims 1-4, 6, 10, 11, 14, 17, 18, 21 and 22 as follows:

1. (Amended) A method of manufacturing a semiconductor device, comprising the steps of:

irradiating a non-single crystalline silicon film with laser light to crystallize the non-single crystalline silicon film; and

thermally annealing the crystallized silicon film to decrease a spin density in the crystallized silicon film

[selectively introducing a metal element for accelerating crystallization into an amorphous silicon film; and

irradiating the silicon film with laser light or strong light].

2. (Amended) A method for producing a semiconductor device, comprising the steps of:

irradiating a non-single crystalline silicon film with laser light to crystallize the non-single crystalline silicon film; and

thermally annealing the crystallized silicon film to decrease dangling bonds in the crystallized silicon film [The method according to claim 1,

wherein the metal element is one or a plurality of elements selected from the group consisting of Fe, Co, Ni, Ru, Rh Pd, Os, Ir, Pt, Cu, Ag and Au].

A1
broader

See
SDI

broader

no metal introduced

? metal impurity
? defect

irradiating will
cause thermal
annealing

according to p.12
spin density in Fig 8
corresponds to
dangling bonds

inherently
needs
m, 1
See Fig 8,
supp 4